

New Jersey Semi-Conductor Products, Inc.

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Silicon NPN Power Transistor

2SC4883

DESCRIPTION

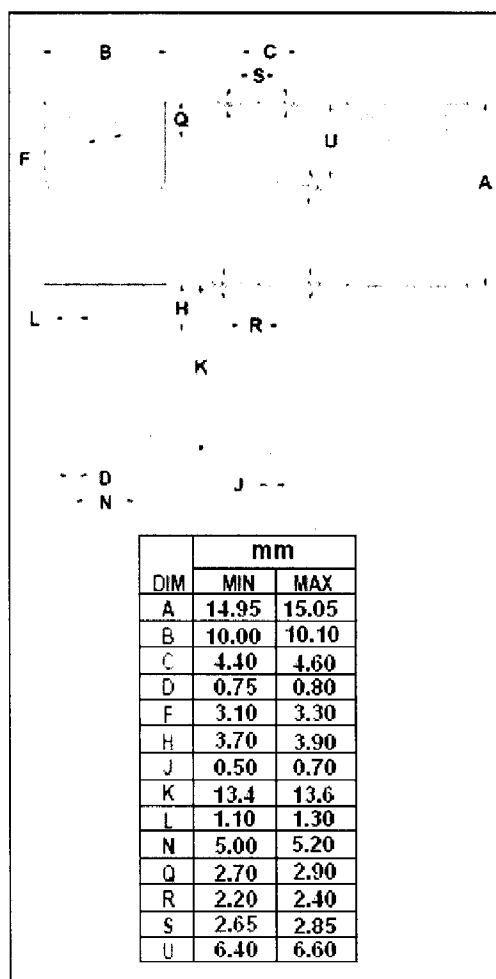
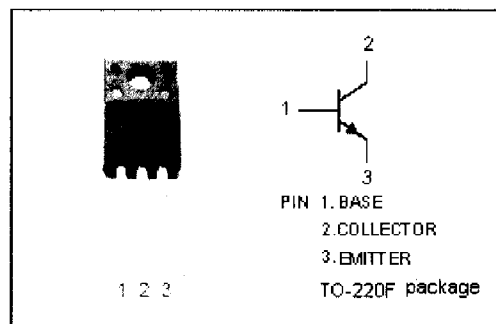
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 150V(\text{Min})$
- Complement to Type 2SA1859

APPLICATIONS

- For audio output driver and TV velocity-modulation applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	2	A
I_B	Base Current-Continuous	1	A
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	20	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=0.7\text{A}; I_B=70\text{mA}$			1.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=150\text{V}; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			10	μA
h_{FE}	DC Current Gain	$I_C=0.7\text{A}; V_{CE}=10\text{V}$	60		240	
f_T	Current-Gain—Bandwidth Product	$I_E=-0.7\text{A}; V_{CE}=12\text{V}$		120		MHz
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1.0\text{MHz}$		30		pF

Switching times

t_{on}	Turn-on Time	$I_C=1\text{A}; I_{B1}=-I_{B2}=-0.1\text{A};$ $R_L=20\Omega; V_{CC}=20\text{V}$		0.5		μs
t_{stg}	Storage Time			1.5		μs
t_f	Fall Time			0.5		μs